

**IN THE CLAIMS**

1. (Previously Presented) A semiconductor laser light emitting device comprising:

a stack of group III nitride semiconductor films;

wherein each group III nitride semiconductor film comprises an element selected from the group consisting of aluminum, gallium, indium, and boron;

wherein, an upper portion of said stack of group III nitride semiconductor films is formed into a ridge-like stripe, to form a current injection region;

wherein a current injection width  $W_{st}$  of said current injection region is at a value in a range of  $1\text{ }\mu\text{m} \leq W_{st} \leq 3\text{ }\mu\text{m}$ ; and

wherein said current injection region is formed on an active layer;

a current non-injection region formed on both sides of said ridge-like strip current injection region, wherein said current non-injection region comprises a material expressed by a chemical formula  $\text{Al}_x\text{Ga}_{1-x}\text{N}$ , wherein the component ratio "x" of Al is at a value in a range of  $0.3 \leq x \leq 1.0$ ; and

a film located between the active layer and the current non-injection region, comprising a material expressed by a chemical formula  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0.3 \leq x \leq 1.0$ ), and having a combined thickness of less than or equal to  $0.2\text{ }\mu\text{m}$  but greater than zero.

Claims 2-4 (Cancelled)

5. (Original) A semiconductor laser light emitting device according to claim 1, wherein a difference  $\Delta n$  between an effective refractive index  $n_1$  of said current injection region

in the film stacking direction and an effective refractive index  $n_2$  of said current non-injection region in the film stacking direction is in a range of  $0.007 \leq \Delta n = (n_1 - n_2) \leq 0.012$ .

Claims 6-8 (Cancelled)

9. (Previously Presented) A semiconductor laser light emitting device comprising:  
a stack of group III nitride semiconductor films;  
wherein each group III nitride semiconductor film comprises an element selected from the group consisting of aluminum, gallium, indium, and boron;  
wherein, an upper portion of said stack of group III nitride semiconductor films comprises is formed into a ridge-like stripe, to form a current injection region;  
wherein a current injection width  $W_{st}$  of said current injection region is at a value in a range of  $1 \mu\text{m} \leq W_{st} \leq 3 \mu\text{m}$ ; and  
wherein said current injection region is formed on an active layer;  
a current non-injection region formed on both sides of said ridge-like strip current injection region, wherein said current non-injection region comprises a material expressed by a chemical formula  $\text{Al}_x\text{Ga}_{1-x}\text{N}$ , wherein the component ratio "x" of Al is at a value in a range of  $0.15 < x < 0.30$ ; and  
wherein the group III nitride semiconductor films located between the active layer and the current non-injection region, comprises a material expressed by a chemical formula  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0.15 \leq x \leq 0.30$ ), and have a combined thickness of less than or equal to  $0.2 \mu\text{m}$  but greater than zero.

Claims 10-12 (Cancelled)

13. (Original) A semiconductor laser light emitting device according to claim 9, wherein a difference  $\Delta n$  between an effective refractive index  $n_1$  of said current injection region in the film stacking direction and an effective refractive index  $n_2$  of said current non-injection region in the film stacking direction is in a range of  $0 < \Delta n = (n_1 - n_2) < 0.007$ .

Claims 14-29 (Cancelled)

30. (Previously Presented) A semiconductor laser light emitting device comprising:  
a stack of group III nitride semiconductor films;

wherein each group III nitride semiconductor film comprises an element selected from the group consisting of aluminum, gallium, indium, and boron;

wherein, an upper portion of said stack of group III nitride semiconductor films forms a ridge-like stripe for a current injection region;

wherein a current non-injection region formed on both sides of said ridge-like strip current injection region, wherein said current non-injection region comprises a material expressed by a chemical formula  $Al_xGa_{1-x}N$ ; and

a film located between an active layer and the current non-injection region, comprising a material expressed by a chemical formula  $Al_xGa_{1-x}N$  ( $0.15 \leq x \leq 0.30$ ), and having a combined thickness of less than or equal to  $0.2 \mu m$  but greater than zero.